

Data Sheet 1340 Rev.B

Features

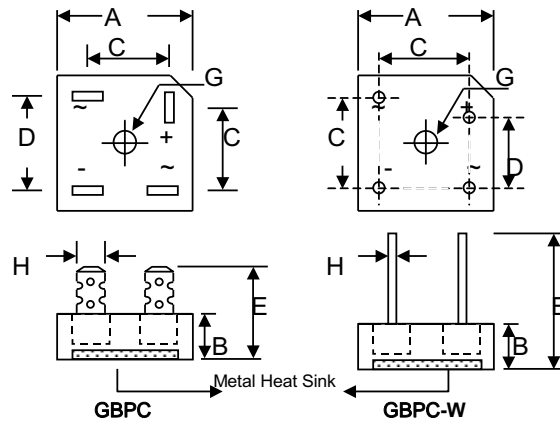
- Glass Passivated Die Construction
- Low Reverse Leakage Current
- Low Power Loss, High Efficiency
- Electrically Isolated Epoxy Case for Maximum Heat Dissipation
- Case to Terminal Isolation Voltage 2500V
- UL Recognized File # E223064

Mechanical Data

- Case: Epoxy Case with Heat Sink Internally Mounted in the Bridge Encapsulation
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Symbols Marked on Case
- Mounting: Through Hole for #8 Screw
- Weight: GBPC 24 grams (approx.)
GBPC-W 21 grams (approx.)
- Marking: Type Number

"W" Suffix Designates Wire Leads
No Suffix Designates Faston Terminals

*All Models are Available on B(Height)=7.62mm Max. Epoxy Case



Dim	GBPC		GBPC		GBPC-W		GBPC-W	
	Min	Max	Min	Max	Min	Max	Min	Max
A	28.40	28.70	1.118	1.130	28.40	28.70	1.118	1.130
B	10.97	11.23	0.432	0.442	10.97	11.23	0.432	0.442
C	15.70	16.70	0.618	0.657	17.10	19.10	0.673	0.752
D	17.50	18.50	0.689	0.728	10.90	11.90	0.429	0.469
E	22.86	25.40	0.90	1.00	30.50	—	1.201	—
G	Hole for #8 screw, 4.90mm(0.193inch)ØNormina							
H	6.35 Typical		0.25 Typical		0.97Ø	1.07Ø	0.038Ø	0.042Ø
	In mm		In inch		In mm		In inch	

Maximum Ratings and Electrical Characteristics @ $T_A=25^\circ\text{C}$ unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristics	Symbol	-00/W	-01/W	-02/W	-04/W	-06/W	-08/W	-10/W	Unit
Peak Repetitive Reverse Voltage	V_{RRM}								V
Working Peak Reverse Voltage	V_{RWM}	50	100	200	400	600	800	1000	
DC Blocking Voltage	V_R								
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Average Rectifier Output Current @ $T_C = 55^\circ\text{C}$	I_o				40				A
					50				
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave Superimposed on rated load (JEDEC Method)	I_{FSM}				400				A
					400				
Forward Voltage Drop (per element)	V_{FM}				1.1				V
Peak Reverse Current At Rated DC Blocking Voltage	I_{RM}				5.0				μA
					500				

SENSITRON
SEMICONDUCTOR

GBPC40, 50/W SERIES
40, 50A GLASS PASSIVATED BRIDGE RECTIFIER

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Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Typical Junction Capacitance (per element) (Note 1)	C _j	300	pF
Typical Thermal Resistance Junction to Case (per element) (Note 2)	R _{θJC}	1.5	K/W
RMS Isolation Voltage from Case to Lead	V _{ISO}	2500	V
Operating and Storage Temperature Range	T _j , T _{STG}	-65 to +150	°C

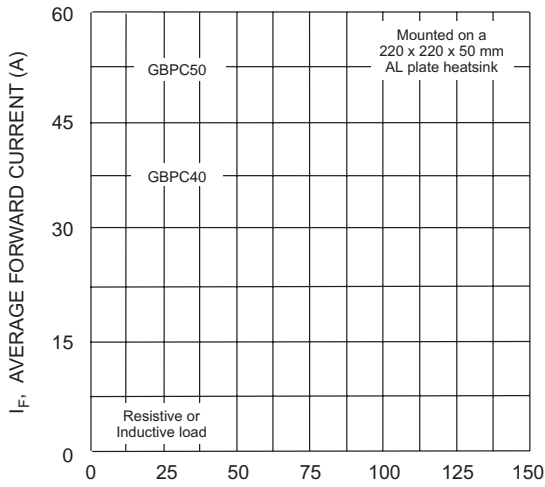
Note: 1. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.
2. Thermal resistance junction to case mounted on heatsink.

SENSITRON SEMICONDUCTOR

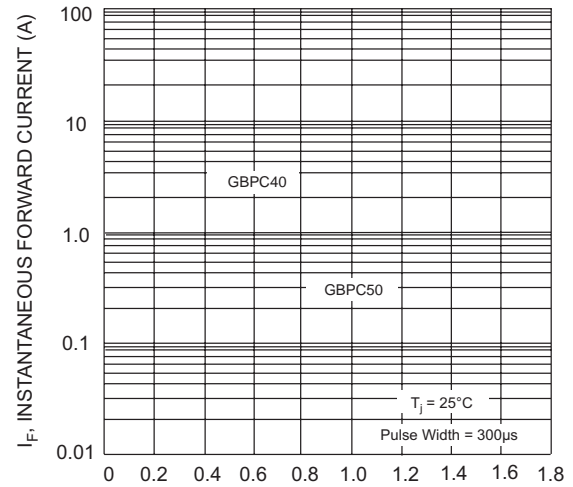
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GBPC40, 50/W SERIES

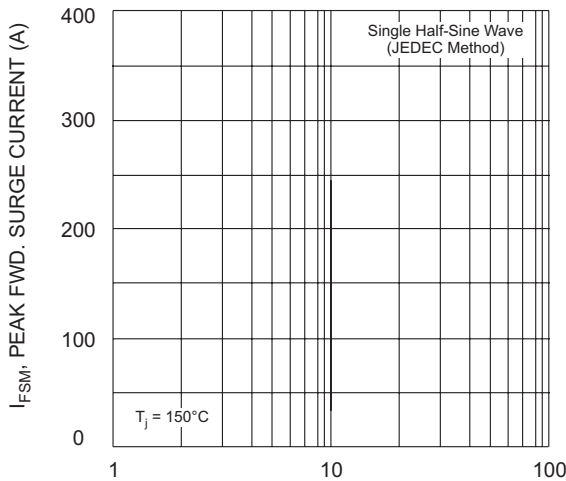
40, 50A GLASS PASSIVATED BRIDGE RECTIFIER



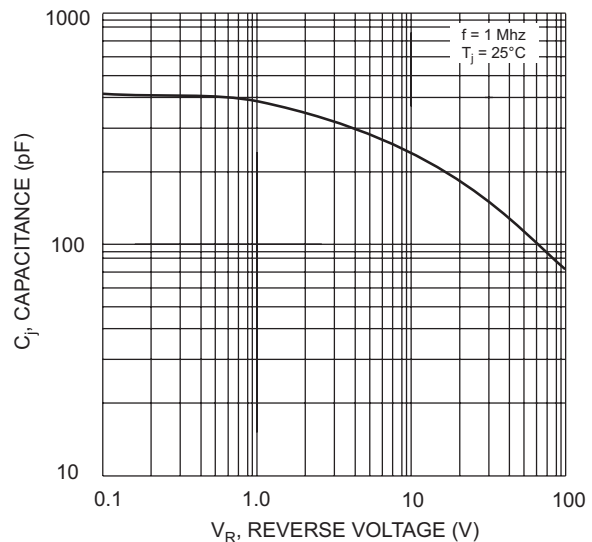
T_C , CASE TEMPERATURE ($^{\circ}C$)
Fig. 1 Forward Current Derating Curve



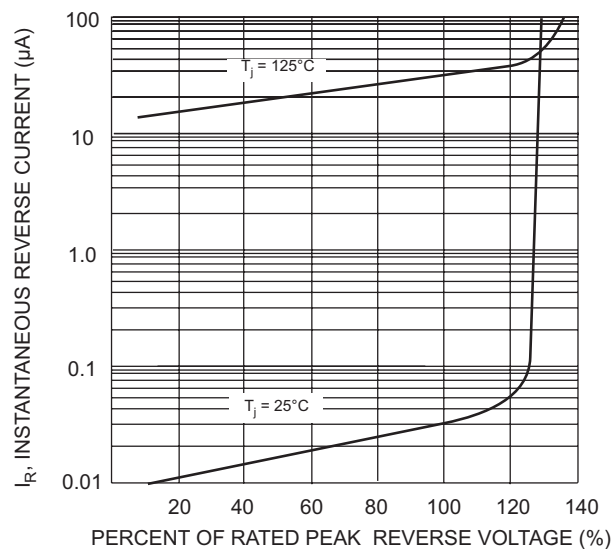
V_F , INSTANTANEOUS FORWARD VOLTAGE (V)
Fig. 2 Typical Forward Characteristics (per element)



NUMBER OF CYCLES AT 60 Hz
Fig. 3 Max Non-Repetitive Surge Current



V_R , REVERSE VOLTAGE (V)
Fig. 4 Typical Junction Capacitance (per element)



PERCENT OF RATED PEAK REVERSE VOLTAGE (%)
Fig. 5 Typical Reverse Characteristics (per element)

TECHNICAL DATA

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